

10/639942

1 of C



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hussein I. Hanafi, et al.

Docket: 15949

Patent No: 7,018,873

Dated: June 20, 2006

Issued: March 28, 2006

**For: METHOD OF MAKING A DEVICE THRESHOLD
CONTROL OF FRONT-GATE SILICON-ON-INSULATOR
MOSFET USING A SELF-ALIGNED BACK-GATE**

**Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

REQUEST FOR CERTIFICATE OF CORRECTION

Sir:

**It appearing that errors have been introduced in the course
of printing the Patent issued in the above application, it is respectfully
requested that the Commissioner issue a Certificate of Correction in
the following respects:**

**57) Abstract
"provides SOI CMOS"**

should read

--The present invention provides SOI CMOS--

**Certificate
of Correction
JUN 26 2006**


**Column 11, Line 19, Claim 17:
"forming suicide" should read -- forming silicide --**

JUN 26 2006

Column 12, Line 20, Claim 19:

“polySi gates and the” should read -- polySi gate and the --

Respectfully submitted,


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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

PATENT NO : 7,018,873
APPLICATION NO : 10/639,942
ISSUE DATE : March 28, 2006
INVENTOR(S) : Hussein I. Hanafi, et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

57) Abstract
"provides SOI CMOS"

should read

--The present invention provides SOI CMOS --

Column 11, Line 19, Claim 17:
"forming suicide" should read -- forming silicide --

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"polySi gates and the" should read -- polySi gate and the --

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PATENT No. 7,018,873

No. of additional copies

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